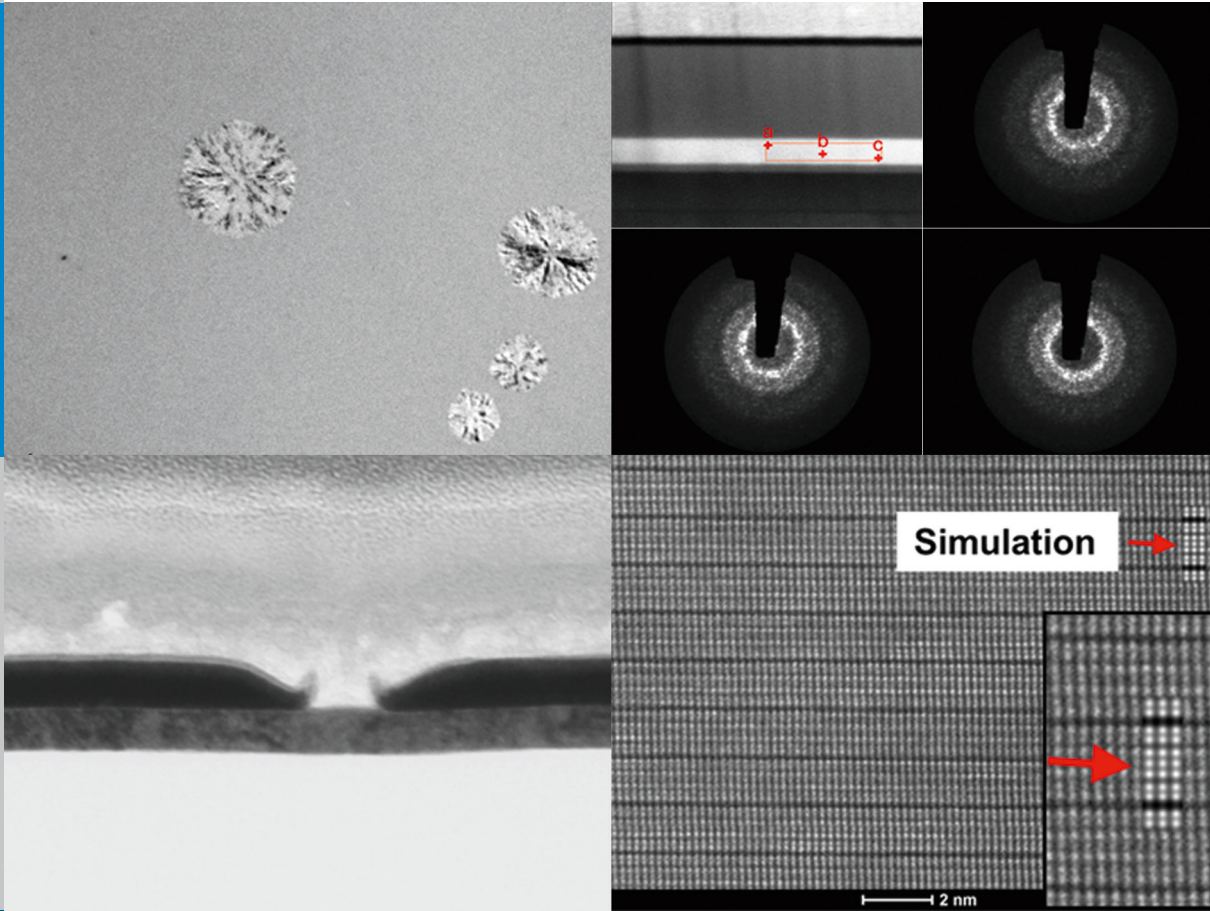


TEM/STEM Investigations of Phase Change Materials for Non-volatile Memory Applications

Manuel Bornhöfft



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